MA10704

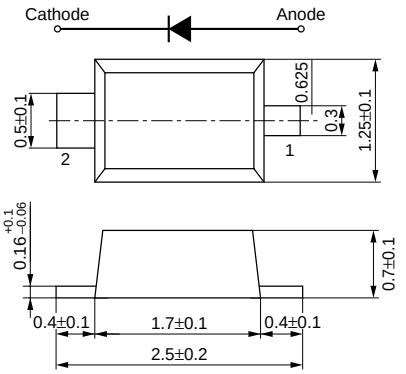
Silicon epitaxial planer type

For high-frequency rectification

■ Features

- S-Mini type package (2-pin)
- $I_{F(AV)}$= 200mA rectification possible
- Low I_R (reverse current) type. (About 1/10 of ordinary product)

Unit : mm



1 : Anode
2 : Cathode
S-Mini Type Package (2-pin)

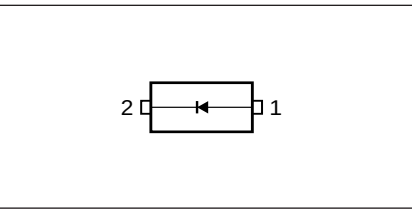
Marking Symbol : 2S

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Non-repetitive peak forward surge current	I_{FSM}*	1	A
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to + 125	˚C

* 50Hz sine wave, one-cycle wave, high value (non-repetitive)

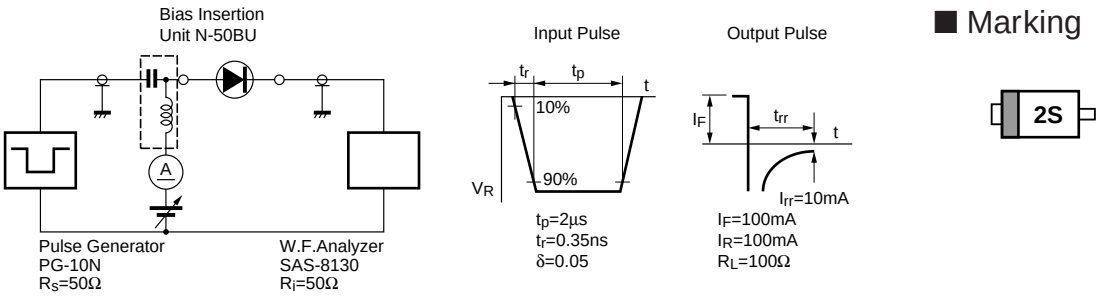
■ Internal Connection



■ Electrical Characteristics (Ta= 25˚C)

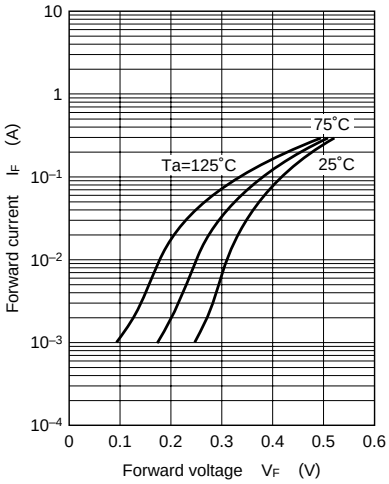
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_{R1}	V_R= 10V			2	µA
	I_{R2}	V_R=20V			5	µA
Forward voltage (DC)	V_F	I_F= 200mA			0.55	V
Terminal capacitance	C_t	V_R= 0V, f =1MHz		30		pF
Reverse recovery time	t_{rr}*	$I_F = I_R$ =100mA I_{rr}= 0.1 · I_R, R_L= 100Ω		3.0		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 1000MHz
3. * t_{rr} measuring circuit

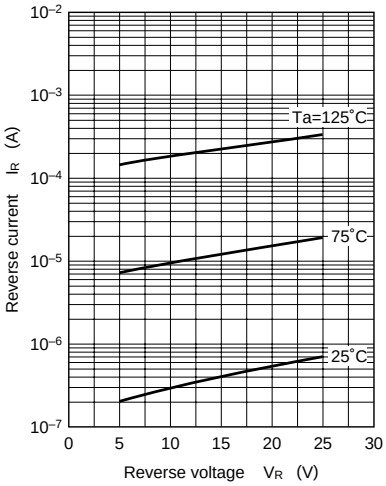


■ Marking

$I_F - V_F$



$I_R - V_R$



$C_t - V_R$